

22nm FD-SOI Circuit Design Techniques for 5G 28GHz Applications

Globalfoundries mmW Design Enablement Team

- Peak $f_t \cdot g_m / I$ at low current density
- Single-stage high gain stacking PA
- Ultra low $R_{ON} C_{OFF}$ RF switch
- g_m / g_{ds} , LDE, $1/f$, self-heating, reliability, Electromigration, A_{Vt} , low C_{sb} / C_{db} , calibrations and RF assist using back-gate

